

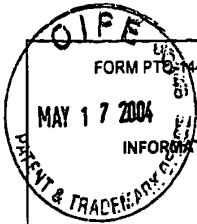
FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MICRON.098CDV2	APPLICATION NO. <u>Unknown</u> 18/615,524
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)		APPLICANT Basceri et al.	
		FILING DATE Herewith 3 JUL 93	GROUP <u>Unknown</u> 2823

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
QWB	1	5,335,138	8/2/94	Sandhu et al.	361	383	A
QWB	2	5,406,445	4/11/95	Fujii et al.	361	385	
QWB	3	5,506,166	4/9/96	Sandhu et al.	438	390	
QWB	4	5,717,234	2/10/98	Si et al.	257	295	
QWB	5	5,781,404	7/14/98	Summerfelt et al.	361	321.5	
QWB	6	5,783,253	7/21/98	Roh	427	81	
QWB	7	5,889,299	3/30/99	Abe et al.	257	295	
QWB	8	5,973,911	10/26/99	Nishioka	361	313	
QWB	9	6,010,931	1/4/00	Sun et al.	438	40	
QWB	10	6,117,482	9/12/00	Kawahara et al.	427	48	
QWB	11	6,136,639	10/24/00	Seon	438	238	
QWB	12	6,319,764 B1	11/20/01	Basceri et al.	438	240	J

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
QWB	13	Hiroshi Itoh et al., "Integration of BST Thin Film for Dram Fabrication", Integrated Ferroelectrics, 1995 Vol. 11, pp 101-109
QWB	14	C. Basceri, "An Important Failure Mechanism in MOCVD (Ba,Sr)TiO ₃ Thin Films: Resistance Degradation", Ferroelectric Thin Films IV, Materials Research Society, Symposium Proceedings Volume 493, 1998, pp. 9-14
QWB	15	Chung Ming Chu and Pang Lin, "Electric Properties and Crystal Structure of a (Ba,Sr)TiO ₃ Films Prepared at Low Temperatures on a LaNiO ₃ Electrode by Radio-Frequency Magnetron Sputtering", Appl. Phys. Lett., Vol. 70 (2), 13 January 1997, pp.249-51
	16	
	17	

O:\DOCS\IJMLJM-2382.DOC
061903

EXAMINER William M. Brunner	DATE CONSIDERED 14 APR 93
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED. INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.	



SHEET 1 OF 1

FORM PTO-1449 MAY 17 2004 INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MICRON.098CDV2	APPLICATION NO. 10/815,524
		APPLICANT Basceri et al.	
		FILING DATE July 3, 2003	GROUP 2823

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
9/B	1.	6,285,051	09/04/01	Ueda et al.	257	296	

FOREIGN PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	

O:\DOCS\LJMLJM-3840.DOC:cbm
051104

EXAMINER <i>William M. Brewster</i>	DATE CONSIDERED <i>14 APR 05</i>
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.	

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Multiple sheets used when necessary) SHEET 1 OF 1	Application No.	10/615,524
	Filing Date	July 3, 2003
	First Named Inventor	Basceri et al.
	Art Unit	2823
	Examiner	William M. Brewster
	Attorney Docket No.	MICRON.098CDV2

PATENT DOCUMENTS					
Examiner Initials	Cite No.	Document Number Number - Kind Code (if known) Example: 1,234,567 B1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear
W/B	1.	6,852,593	02/08/05	Basceri et al. 438/253	X
W/B	2.	6,855,971	02/15/05	Basceri et al. 257/295	X

FOREIGN PATENT DOCUMENTS						
Examiner Initials	Cite No.	Foreign Patent Document Country Code-Number-Kind Code Example: JP 1234567 A1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear	T ¹
W/B	3.	EPO 0 617 439 A2	03-24-1994	Matsushita Electric Industrial Co.	X	A
W/B	4.	JP 406 333 772A	12-02-1994	Fujii et al.	X	X

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ¹
W/B	5.	Copy of Claims as allowed in Amendment filed August 14, 2004 in Application No. 10/614,418, filed July 3, 2003	X
W/B	6.	Copy of March 14, 2003 Office Action in U.S. Patent No. 6,855,971 causing JP 406 333 772A to be listed.	X

JTE\JTE-1926.DOC
022205

Examiner Signature <i>William M. Brewster</i>	Date Considered <i>14 APR 05</i>
*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

T¹ - Place a check mark in this area when an English language Translation is attached.